

# 15 A, 600 V, STEALTH™ II Diode

# **FFPF15S60S**

## **Description**

The FFPF15S60S is STEALTH™ II rectifier with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

#### **Features**

- Stealth Recovery  $T_{rr}$ = 35 ns (@  $I_F$ = 15 A)
- Max Forward Voltage,  $V_F = 2.6 \text{ V}$  (@  $T_C = 25^{\circ}\text{C}$ )
- 600 V Reverse Voltage and High Reliability
- Improved dv/dt Capability
- This Device is Pb-Free and is RoHS Compliant

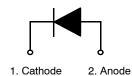
# **Applications**

- General Purpose
- Switching Mode Power Supply
- Boost Diode in Continuous Mode Power Factor Corrections
- Power Switching Circuits

# ABSOLUTE MAXIMUM RATINGS T<sub>C</sub> = 25°C unless otherwise noted

| Symbol                            | Parameter  | Value   | Unit |  |
|-----------------------------------|--|---------|------|--|
| $V_{RRM}$                         | Peak Repetitive Reverse Voltage 600                              |         |      |  |
| $V_{RWM}$                         | Working Peak Reverse Voltage                                     | 600     | V    |  |
| $V_R$                             | DC Blocking Voltage  | age 600 |      |  |
| I <sub>F(AV)</sub>                | Average Rectified Forward Current<br>@ T <sub>C</sub> = 52°C     | 15      | Α    |  |
| I <sub>FSM</sub>                  | Non-repetitive Peak Surge Current<br>60 Hz Single Half-Sine Wave |         |      |  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature – 65 to +175 Range             |         | °C   |  |

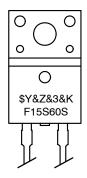
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.





**TO-220F-2L CASE 221AS** 

#### **MARKING DIAGRAM**



\$Y = **onsemi** Logo

&Z&3 = Date Code (Year & Week)

&K = Lc

F15S60S = Specific Device Code

#### **ORDERING INFORMATION**

| Device       | Package    | Shipping  |
|--------------|------------|-----------|
| FFPF15S60STU | TO-220F-2L | 50 / Tube |

#### **FFPF15S60S**

#### THERMAL CHARACTERISTICS

| Symbol         | Parameter                                    | Value | Unit |
|----------------|--|-------|------|
| $R_{	heta JC}$ | Maximum Thermal Resistance, Junction to Case | 4.6   | °C/W |

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25 °C unless otherwise noted)

| Symbol  | Parameter   |   | Min.        | Тур.                    | Max               | Unit          |
|---|---|---|-------------|-------------------------|-------------------|---------------|
| V <sub>FM</sub> (Note 1)  | I <sub>F</sub> = 15 A<br>I <sub>F</sub> = 15 A  | $T_C = 25$ °C<br>$T_C = 125$ °C                 |             | 2.1<br>1.6              | 2.6<br>-          | V             |
| I <sub>RM</sub> (Note 1)  | V <sub>R</sub> = 600 V<br>V <sub>R</sub> = 600 V  | T <sub>C</sub> = 25°C<br>T <sub>C</sub> = 125°C | -           | -<br>-                  | 100<br>500        | μΑ            |
| t <sub>rr</sub>   | $I_F = 1 \text{ A, di}_F/dt = 100 \text{ A/}\mu\text{s, V}_R = 30 \text{ V}$                          | T <sub>C</sub> = 25°C                           | -           | 21                      | 30                | ns            |
| t <sub>rr</sub><br>I <sub>rr</sub><br>S factor<br>Q <sub>rr</sub> | $I_F = 15 \text{ A}, \text{ di}_F/\text{dt} = 200 \text{ A/}\mu\text{s}, \text{ V}_R = 390 \text{ V}$ | T <sub>C</sub> = 25°C                           |             | 23<br>2.5<br>0.7<br>29  | 35<br>-<br>-<br>- | ns<br>A<br>nC |
| t <sub>rr</sub><br>I <sub>rr</sub><br>S factor<br>Q <sub>rr</sub> | $I_F = 15 \text{ A}, \text{ di}_F/\text{dt} = 200 \text{ A/}\mu\text{s}, \text{ V}_R = 390 \text{ V}$ | T <sub>C</sub> = 125°C                          | -<br>-<br>- | 55<br>4.3<br>1.1<br>118 | -<br>-<br>-       | ns<br>A<br>nC |
| W <sub>AVL</sub>  | Avalanche Energy (L = 40 mH)  |   | 20          | -                       | -                 | mJ            |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **TEST CIRCUIT AND WAVEFORMS**

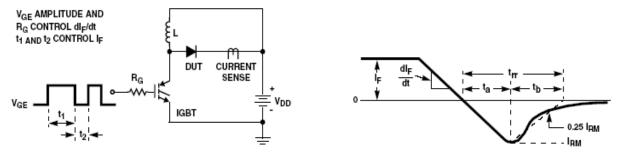


Figure 1. Diode Reverse Recovery Test Circuit & Waveform

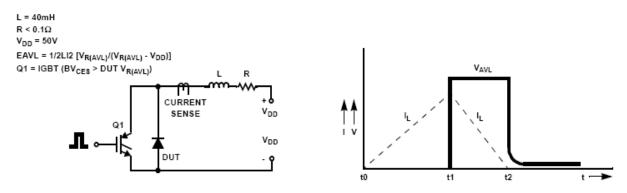


Figure 2. Unclamped Inductive Switching Test Circuit & Waveform

<sup>1.</sup> Pulse: Test Pulse width = 300 μs, Duty Cycle = 2%

#### FFPF15S60S

#### TYPICAL PERFORMANCE CHARACTERISTICS

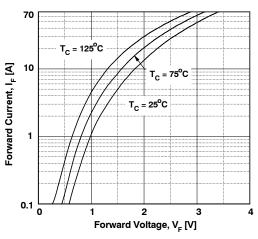


Figure 3. Typical Forward Voltage Drop vs. Forward Current

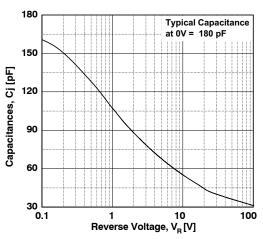


Figure 5. Typical Junction Capacitance

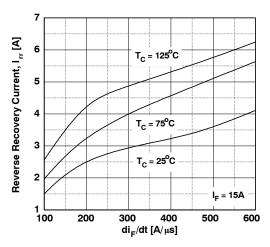


Figure 7. Typical Reverse Recovery Current vs. di/dt

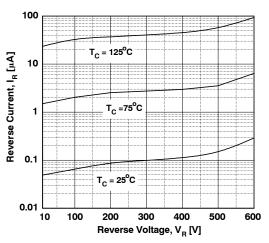


Figure 4. Typical Reverse Current vs. Reverse Voltage

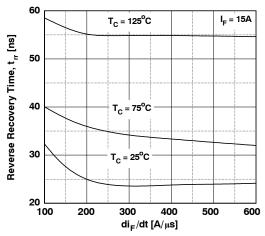


Figure 6. Typical Reverse Recovery Time vs. di/dt

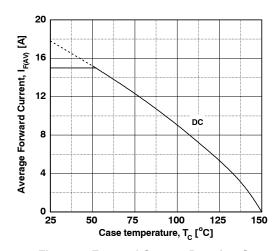


Figure 8. Forward Current Derating Curve

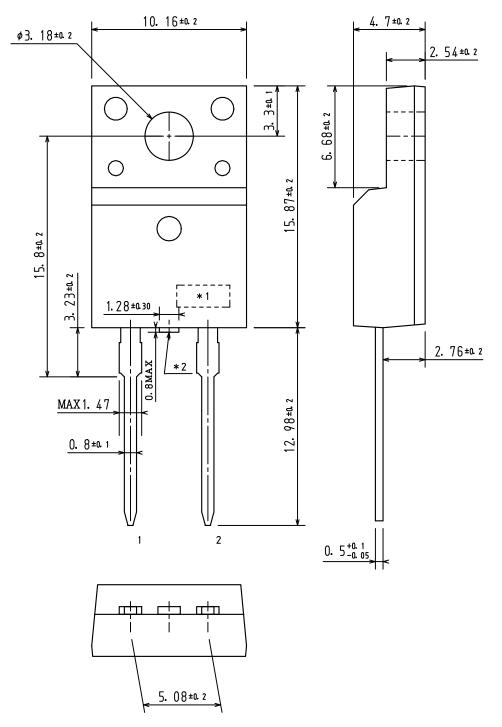
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#### TO-220 Fullpack, 2-Lead / TO-220F-2FS CASE 221AS ISSUE O

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